semiconductor material such that the semiconductor material of the first and second sidewalls is undamaged; and

thermally growing a gate oxide on the first and second sidewalls of the mesa.

23. The method of claim **22** wherein plasma etching comprises an anisotropic etch.

24. A method comprising:

etching, with a first etchant, first and second dielectric regions through first and second openings of a mask layer to create first and second trenches respectively disposed adjacent first and second sidewalls of a mesa of semiconductor material, leaving first and second portions of the first and second dielectric regions respectively covering the first and second sidewalls of the mesa, the mesa eventually comprising an extended drain region of a field-effect transistor; and

etching, with a second etchant, the first and second portions to expose the first and second sidewalls,

wherein the first etchant is substantially anisotropic and the second etchant is substantially isotropic.

25. The method of claim **24** wherein the second etchant is selective with respect to the semiconductor material such that the semiconductor material of the first and second sidewalls is undamaged by the etching.

26. The method of claim **24** wherein the etching by the second etchant is performed through the first and second openings of the mask layer.

* * * * *